



2CK120

SILICON EPITAXIAL
PLANAR SWITCHING DIODE

REVERSE VOLTAGE: 75V

FORWARD CURRENT: 150mA

**TECHNICAL
SPECIFICATION**

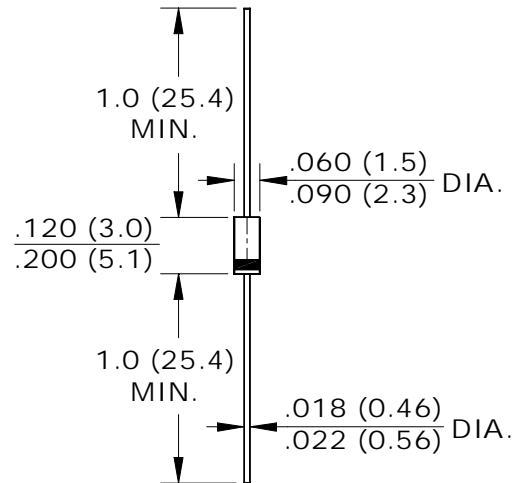
FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed:
250°C/10S/9.5mm lead length
at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per
MIL-STD 202E, method 208C
- Case: Glass, hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

DO - 35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

| RATINGS | SYMBOL | VALUE | UNITS |
|--|------------------|----------|---------------|
| Reverse Voltage | V_R | 75 | V |
| Peak Reverse Voltage | V_{RM} | 100 | V |
| Forward Current (average) | I_O | 150 | mA |
| Repetitive Forward Peak Current | I_{FRM} | 400 | mA |
| Forward Voltage ($I_F=10mA$) | V_F | 1 | V |
| Reverse Current ($V_R=20V$) | I_{R1} | 25 | nA |
| Reverse Current ($V_R=75V$) | | 5 | μA |
| Reverse Current ($V_R=20V, T_J=100^\circ C$) | I_{R2} | 50 | μA |
| Capacitance (note 1) | C_t | 4 | pF |
| Reverse Charge ($I_F=10mA$) | Q_r | 57 | pC |
| Thermal Resistance (junction to ambient, note 2) | $R_{\theta(ja)}$ | 0.35 | $^\circ C/mW$ |
| Operating Junction and Storage Temperature Range | T_{STG}, T_J | -55~+175 | $^\circ C$ |

Notes:

1. $V_R=0V, f=1 MHz$
2. Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.